



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DXTA94

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

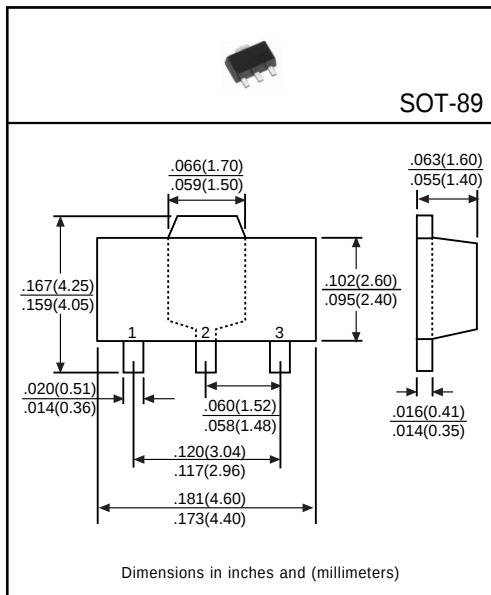
Designed for applications requiring high breakdown voltage.

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-400	V
Collector-Emitter Voltage	V_{CE0}	-400	V
Emitter-Base Voltage	V_{EB0}	-6	V
Collector Current	I_C	-500	mA
Total Power Dissipation	P_D	1	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}\text{C}$



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CB0}	-400	-	-	V	$I_C=-100\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CE0}	-400	-	-	V	$I_C=-1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EB0}	-6	-	-	V	$I_E=-10\mu\text{A}$
Collector Cutoff Current	I_{CBO}	-	-	-100	nA	$V_{CB}=-400\text{V}$
	I_{CES}	-	-	-500	nA	$V_{CE}=-400\text{V}, V_{BE}=0$
Emitter Cutoff Current	I_{EBO}	-	-	-100	nA	$V_{EB}=-6\text{V}$
Collector-Emitter Saturation Voltage ⁽¹⁾	$V_{CE(sat)1}$	-	-	-0.35	V	$I_C=-1\text{mA}, I_B=-0.1\text{mA}$
	$V_{CE(sat)2}$	-	-	-0.5	V	$I_C=-10\text{mA}, I_B=-1\text{mA}$
	$V_{CE(sat)3}$	-	-	-0.75	V	$I_C=-50\text{mA}, I_B=-5\text{mA}$
Base-Emitter Saturation Voltage ⁽¹⁾	$V_{BE(sat)}$	-	-	-0.75	V	$I_C=-10\text{mA}, I_B=-1\text{mA}$
DC Current Gain ⁽¹⁾	h_{FE1}	40	-	-	-	$I_C=-1\text{mA}, V_{CE}=-10\text{V}$
	h_{FE2}	50	-	300	-	$I_C=-10\text{mA}, V_{CE}=-10\text{V}$
	h_{FE3}	45	-	-	-	$I_C=-50\text{mA}, V_{CE}=-10\text{V}$
	h_{FE4}	40	-	-	-	$I_C=-100\text{mA}, V_{CE}=-10\text{V}$

(1)Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$